

# Magneto-transport properties of BaNiS<sub>2</sub> and BaCoS<sub>2</sub> under high pressure up to 10 GPa

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During the 1990s, the quasi-2D BaCo<sub>1-x</sub>Ni<sub>x</sub>S<sub>2</sub> system ( $x = 0$  to 1) has been topic of numerous studies due to its similarity with high- $T_C$  superconducting materials. Its structure consists of electronically active Co(Ni)S sheets sandwiched between BaS layers. The relation between magnetism and transport properties in BaCo<sub>1-x</sub>Ni<sub>x</sub>S<sub>2</sub> is quite complex and not yet understood. As an illustration, the mother compound ( $x = 0$ ) exhibits a paramagnetic to antiferromagnetic transition at  $T_N \sim 300$  K, but without any transition in the transport properties [1]. On the other hand, when doped with Ni, the system undergoes a metal–insulator transition (MIT) at  $x \sim 0.22$  [1]. A systematic study on the two end members of the series (BaNiS<sub>2</sub> and BaCoS<sub>2</sub>) should help to unveil the mechanism of the MIT.

The control of the bandwidth and band-filling are two traditional ways to understand and manipulate the MIT. Experimentally, the bandwidth control can be achieved by applying a high pressure that may provide a tool to adjust the magnetic properties simultaneously.

In that respect, we have carried out magneto-transport measurements under high pressure up to 10 GPa on high quality single-crystals of BaNiS<sub>2</sub> and BaCoS<sub>2</sub>. The resistance is measured down to a temperature of 2 K and under magnetic fields of up to 9 T. Only BaCoS<sub>2</sub> shows an MIT. BaNiS<sub>2</sub> keeps a metallic behavior, except at the lowest temperature where a weak localization is found. The results presented are interpreted with a Debye model.

[1] L. S. Martinson, J. W. Schweitzer, and N. C. Baenziger, *Phys. Rev. Lett.* **71**, 125 (1993).